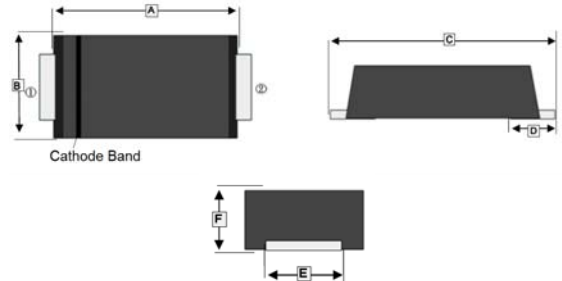


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

SMAM



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	3.20	3.70	D	1 TYP.	
B	2.40	2.80	E	1.30	1.60
C	4.40	4.90	F	0.90	1.20

MECHANICAL DATA

- Case : SMAM
- Terminals: Solderable per MIL-STD-750, Method 2026
- Weight: 27 mg (Approximate)

MARKING

SL545

PACKAGE INFORMATION

Package	MPQ	Leader Size
SMAM	3K	7 inch

ABSOLUTE MAXIMUM RATINGS

(Rating 25°C ambient temperature unless otherwise specified. Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, de-rate current by 20%.)

Parameter	Symbol	Rating	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	45	V
Maximum RMS Voltage	V_{RMS}	32	V
Maximum DC Blocking Voltage	V_{DC}	45	V
Maximum Average Forward Rectified Current	I_F	5	A
Peak Forward Surge Current, 8.3ms single half sine-wave superimposed on rated load	I_{FSM}	150	A
Maximum Instantaneous Forward Voltage @ $I_F=5A$	V_F	0.45	V
Maximum DC Reverse Current at Rated DC Blocking Voltage @ $T_A=25^\circ C$	I_R	0.5	mA
Typical Junction Capacitance ¹	C_J	700	pF
Typical Thermal Resistance ²	$R_{\theta JL}$	22	°C/W
Operating Temperature	T_J	-55~125	°C
Storage Temperature	T_{STG}	-55~150	°C

Notes:

1. Measured at 1MHz and applied reverse voltage of 4 V D.C.
2. P.C.B. mounted with 5X 5cm copper pad areas.

RATINGS AND CHARACTERISTIC CURVES

Fig.1 Forward Current Derating Curve

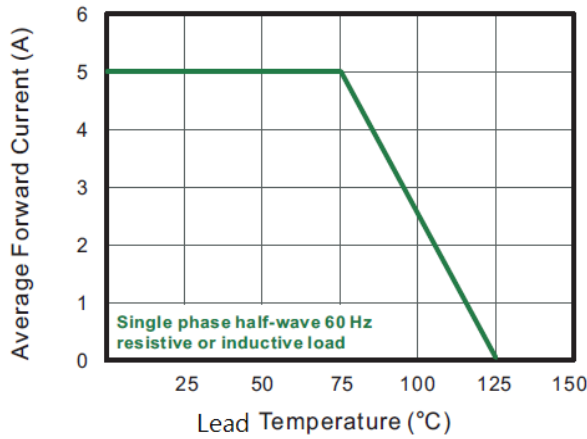


Fig.2 Typical Reverse Characteristics

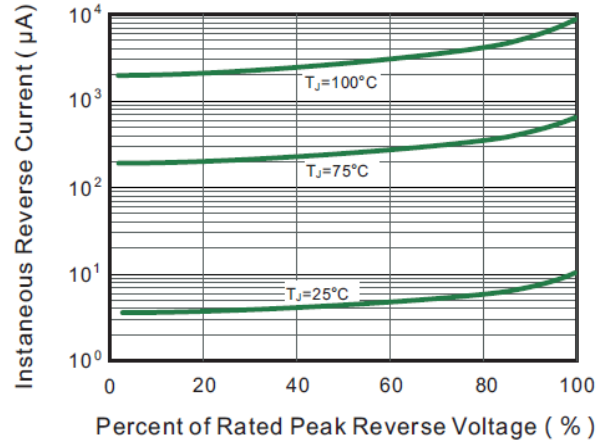


Fig.3 Typical Forward Characteristic

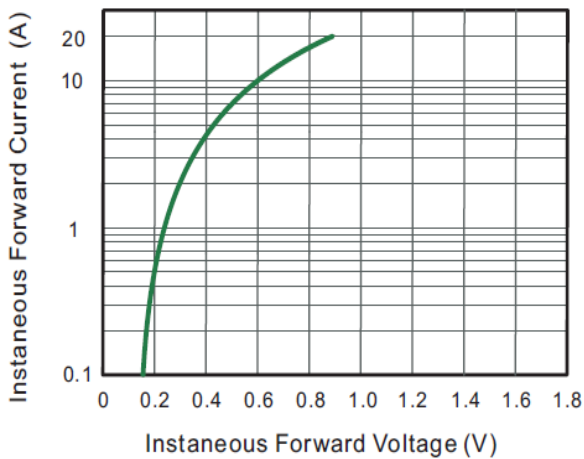


Fig.4 Typical Junction Capacitance

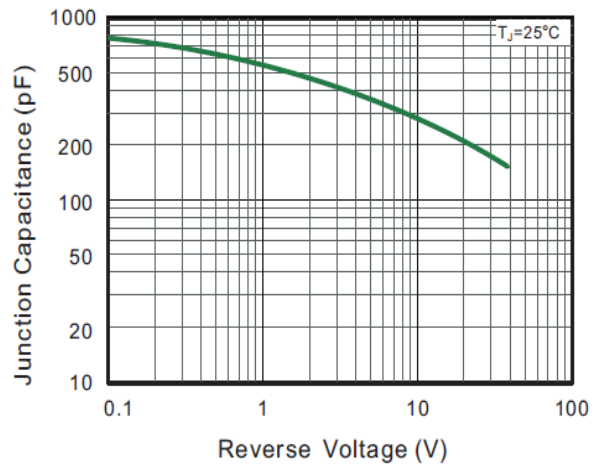


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

